

SEMiX® 6p

## 3-Phase Bridge Rectifier

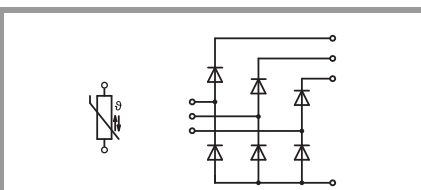
### SEMiX586D16p

#### Features\*

- Terminal height 17 mm
- Chips soldered directly to insulated substrate
- UL recognized file no. E63532
- Press-Fit pins
- NEW SKR PEP diode-technology for enhanced power and environmental robustness
- $T_{jmax} = 175^{\circ}\text{C}$
- NTC temperature sensor

#### Remarks

- Temperature sensor: no basic insulation to main circuit, signal processing with reference to negative DC potential
- Product reliability results valid for  $T_j \leq 150^{\circ}\text{C}$  (recommended  $T_{jop} = -40 \dots 150^{\circ}\text{C}$ )
- All positive DC terminals have to be connected externally to same potential



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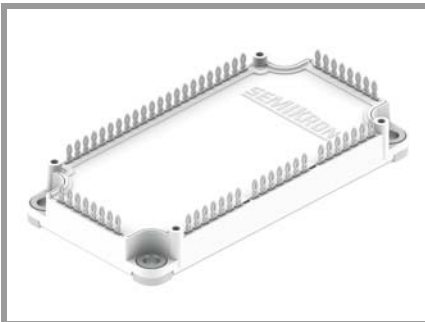
Absolute Maximum Ratings			
Symbol	Conditions	Values	Unit
<b>Module</b>			
$I_{t(RMS)}$	per power terminal (50 A / pin)	700	A
$T_{stg}$		-40 ... 125	$^{\circ}\text{C}$
$V_{isol}$	AC sinus 50Hz, $t = 1 \text{ min}$	4000	V

Absolute Maximum Ratings				
Symbol	Conditions	Values	Unit	
<b>Diode</b>				
$I_{FAV}$	$T_j = 175^{\circ}\text{C}$ sin 180°	$T_c = 85^{\circ}\text{C}$	392	A
		$T_c = 100^{\circ}\text{C}$	344	A
$I_{FSM}$	10 ms sin 180°	$T_j = 25^{\circ}\text{C}$	4800	A
		$T_j = 150^{\circ}\text{C}$	4200	A
$i^2t$	10 ms sin 180°	$T_j = 25^{\circ}\text{C}$	115200	$\text{A}^2\text{s}$
		$T_j = 150^{\circ}\text{C}$	88200	$\text{A}^2\text{s}$
$V_{RSM}$		1700	V	
$V_{RRM}$		1600	V	
$T_j$		-40 ... 175	$^{\circ}\text{C}$	

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
<b>Diode</b>					
$V_F$	$I_F = 238 \text{ A}$ chiplevel	$T_j = 25^{\circ}\text{C}$	0.97	1.20	V
		$T_j = 150^{\circ}\text{C}$	0.84	1.07	V
$V_F$	$I_F = 238 \text{ A}$ terminal level	$T_j = 25^{\circ}\text{C}$	1.07	1.34	V
		$T_j = 150^{\circ}\text{C}$	0.98	1.26	V
$V_{F0}$	chiplevel Approximation for: $I_{F1} = 238 \text{ A}$ $I_{F2} = 714 \text{ A}$	$T_j = 25^{\circ}\text{C}$	0.89	1.09	V
		$T_j = 150^{\circ}\text{C}$	0.73	0.92	V
$r_F$	chiplevel	$T_j = 25^{\circ}\text{C}$	0.34	0.46	$\text{m}\Omega$
		$T_j = 150^{\circ}\text{C}$	0.48	0.65	$\text{m}\Omega$
$I_R$	$T_j = 150^{\circ}\text{C}, V_{RRM}$			5.5	mA
$R_{th(j-c)}$	per diode, cont.			0.12	K/W
$R_{th(j-c)}$	per diode, sin. 180°			0.147	K/W
$R_{th(j-c)}$	per diode, rec. 120°			0.153	K/W
$R_{th(c-s)}$	per diode ( $\lambda_{grease} = 0.81 \text{ W}/(\text{m}^2\text{K})$ )		0.043		K/W

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
<b>Module</b>					
$R_{CC+EE}$	measured per switch	$T_c = 25^{\circ}\text{C}$	0.4		$\text{m}\Omega$
		$T_c = 125^{\circ}\text{C}$	0.6		$\text{m}\Omega$
$R_{th(c-s)1}$	calculated without thermal coupling ( $\lambda_{grease} = 0.81 \text{ W}/(\text{m}^2\text{K})$ )		0.007		K/W
		including thermal coupling, $T_s$ underneath module ( $\lambda_{grease} = 0.81 \text{ W}/(\text{m}^2\text{K})$ )		0.011	
$M_s$	to heat sink (M5)	3		6	Nm
w			300		g

# SEMiX586D16p



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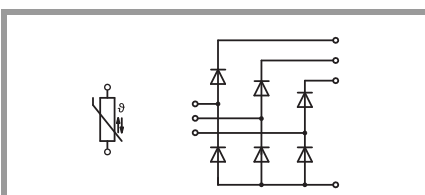
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#### Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
<b>Temperature Sensor</b>					
$R_{100}$	$T_c = 100^{\circ}\text{C}$ ( $R_{25} = 5 \text{ k}\Omega$ )		$493 \pm 5\%$		$\Omega$
$B_{100/125}$	$R(T) = R_{100} \exp[B_{100/125}(1/T - 1/T_{100})]$ ; $T[\text{K}]$		$3550 \pm 2\%$		K



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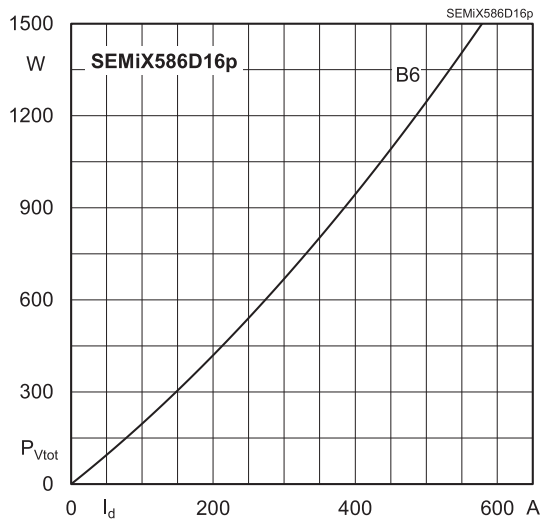


Fig. 4L: Power dissipation per module vs. direct current

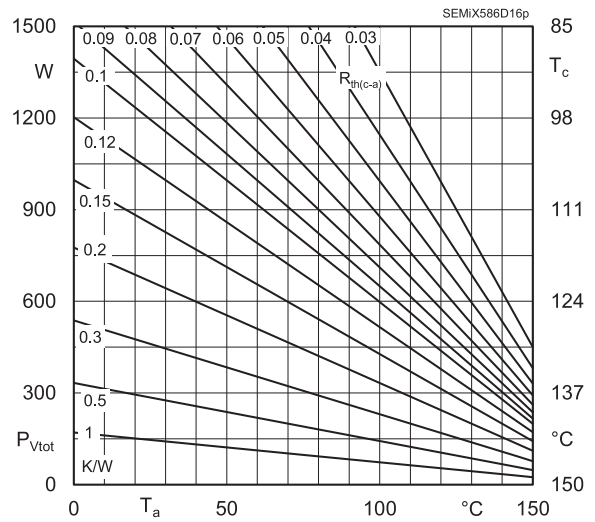


Fig. 4R: Power dissipation per module vs. ambient temperature

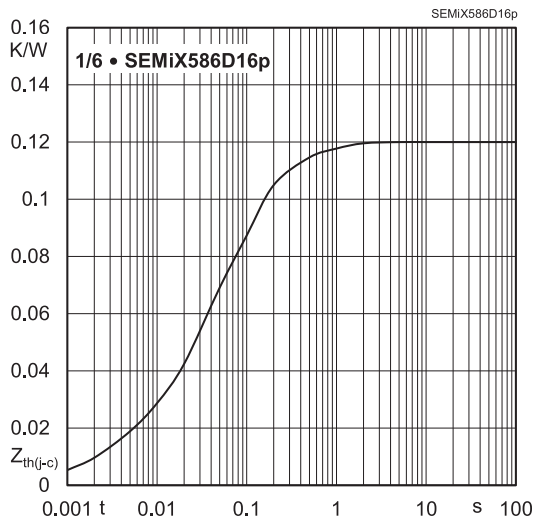


Fig. 6: Transient thermal impedance vs. time

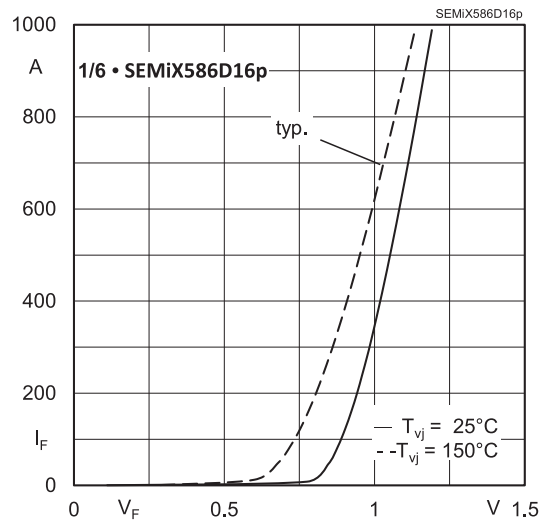


Fig. 7: On-state characteristics (chipllevel)

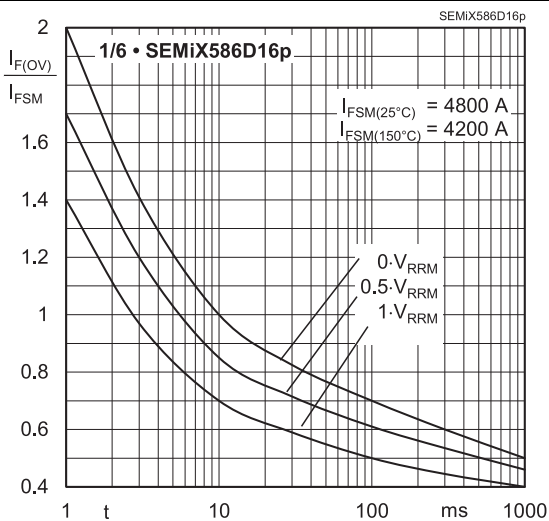
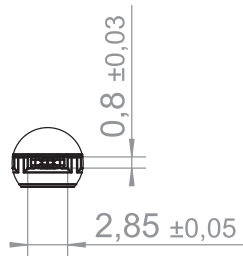
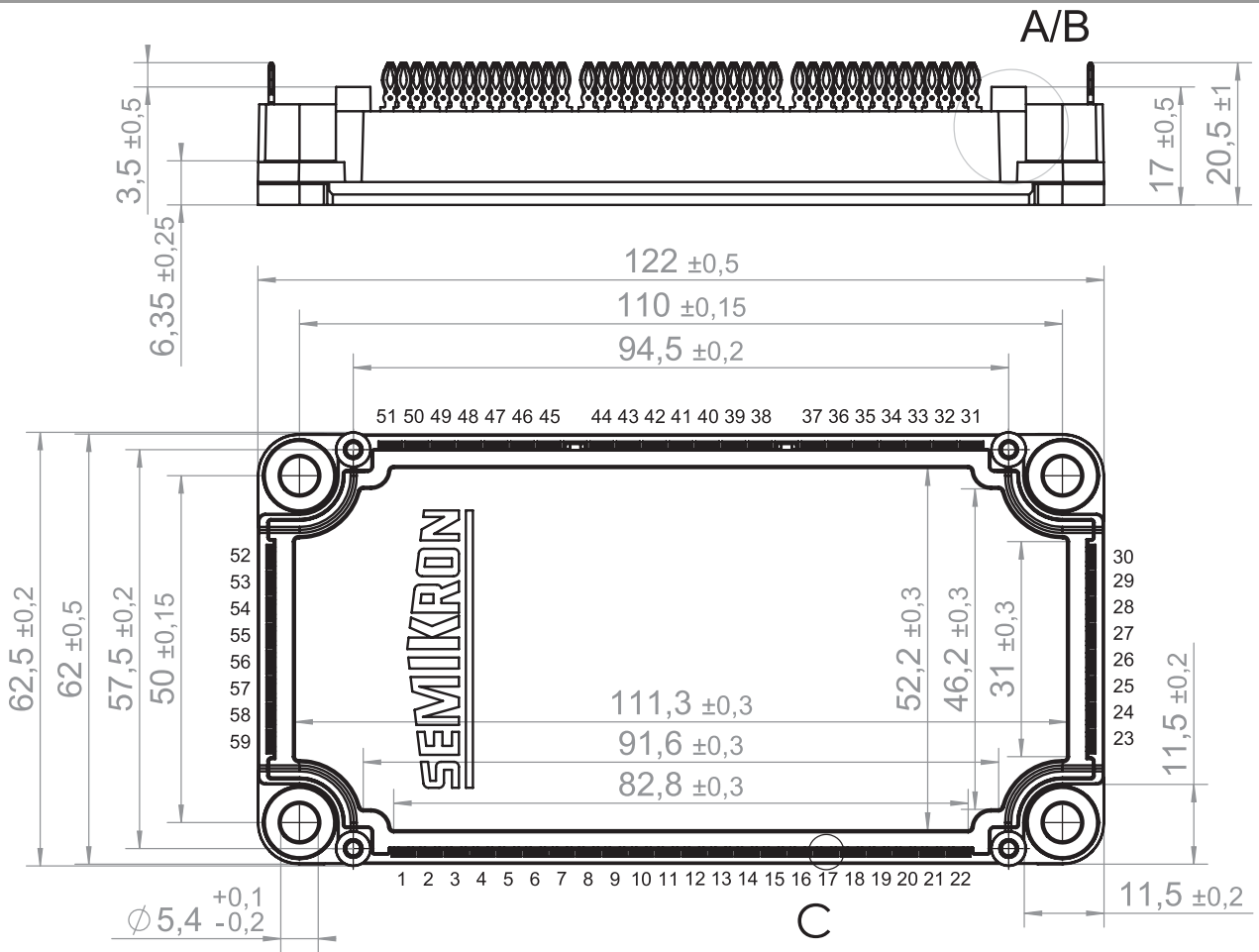
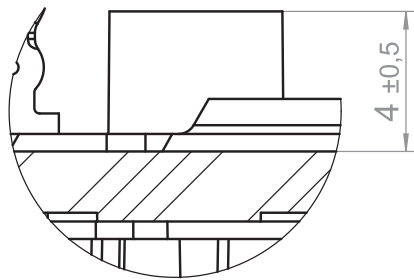


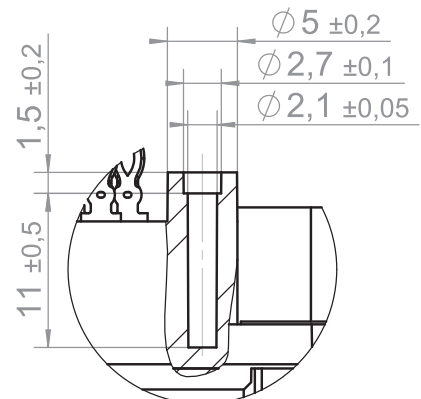
Fig. 8: Surge overload current vs. time



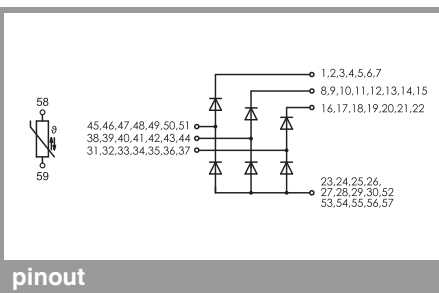
C (2 : 1)



B (5 : 1)  
Cross-sectional plane in the middle of the module

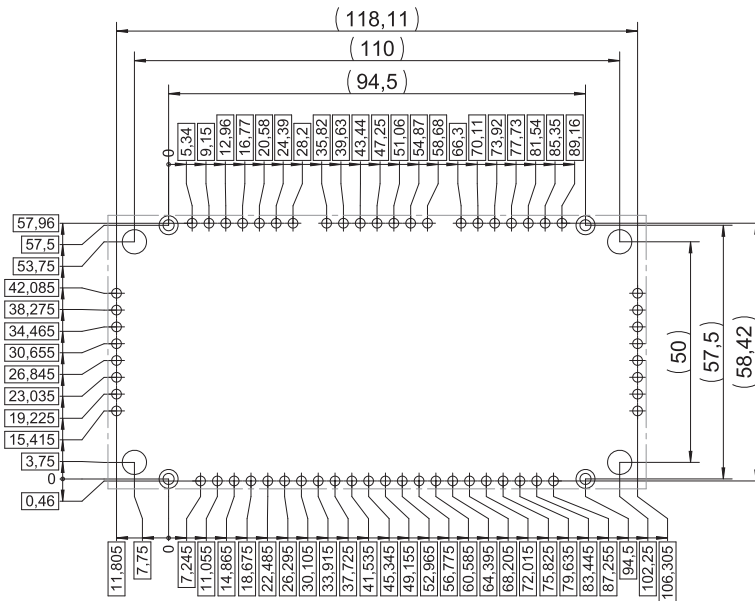


A (2 : 1)  
Cut-out shows section through the center of the PCB-dome



pinout

## PCB drillhole pattern



- Tolerance for PCB holes  $\pm \phi 0,1$
- Diameter of plated holes  $\phi 2,14 \text{ mm} - 2,29 \text{ mm}$
- Diameter of drill  $\phi 2,35 \text{ mm}$

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

### \*IMPORTANT INFORMATION AND WARNINGS

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